

# Cryogenically Cooled Saturating Quasi-ALE of Silicon Nitride

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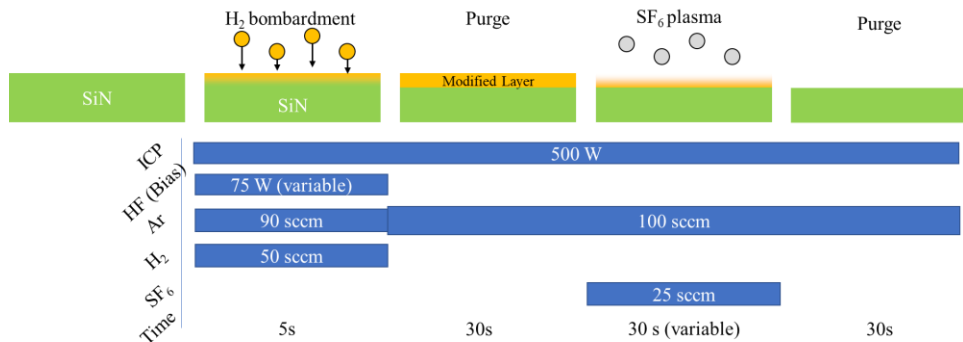


Figure 1: Quasi-ALE SiN Etch Process

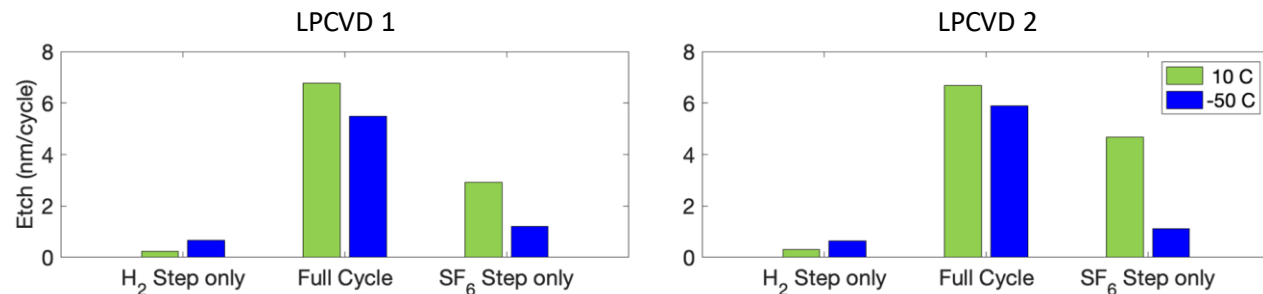


Figure 2: Components Contributing to ALE Synergy vs. Temperature

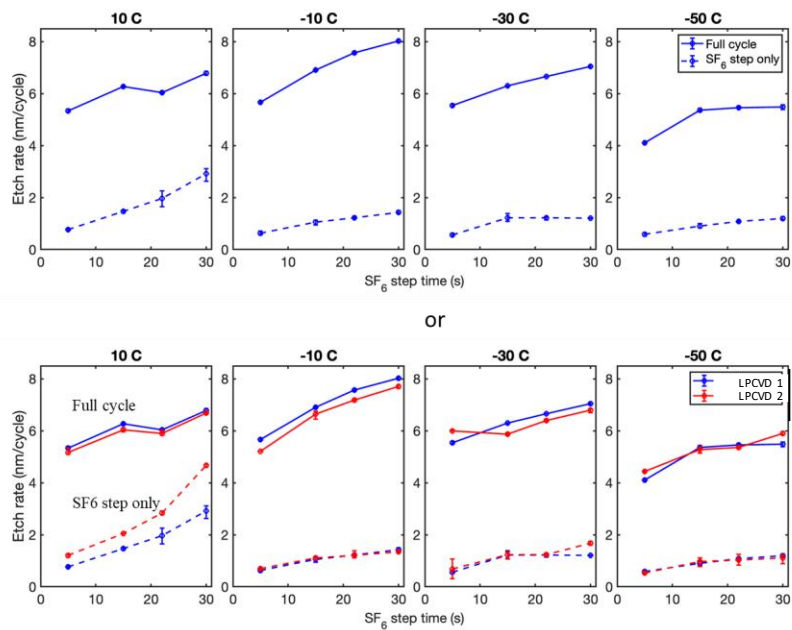


Figure 3: Saturation Curves Vs. Temperature

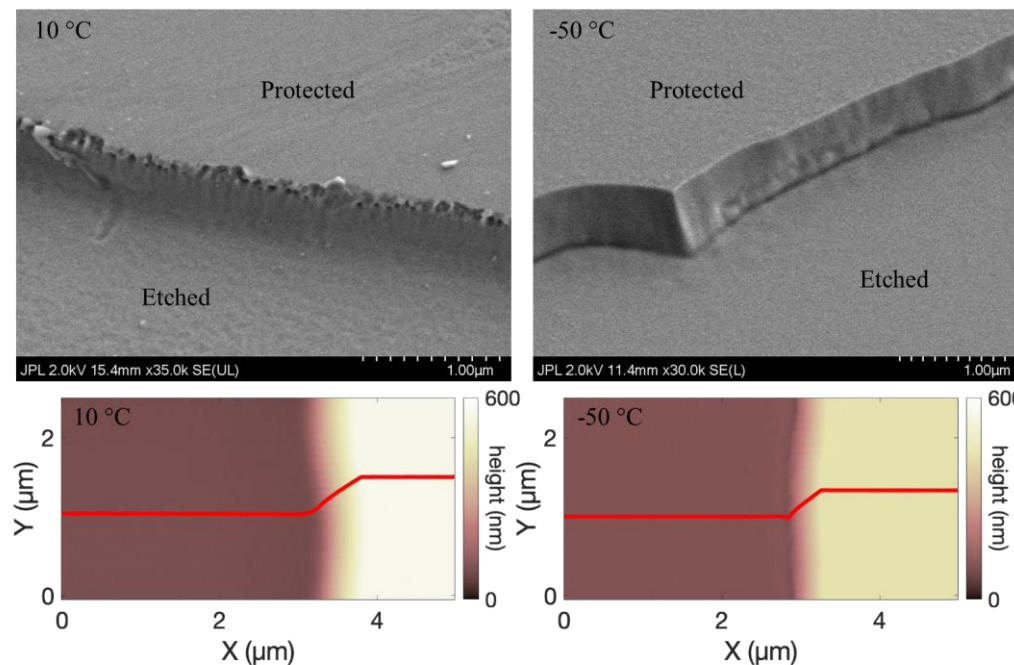


Figure 4: LPCVD1 Etch Profile vs. Temperature

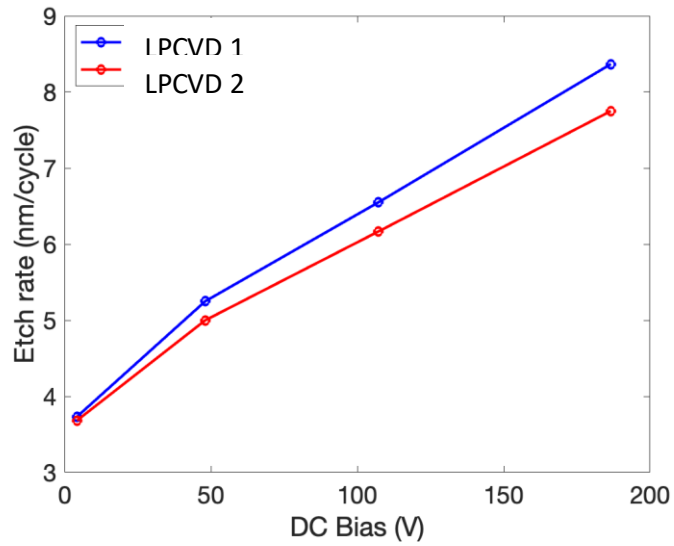
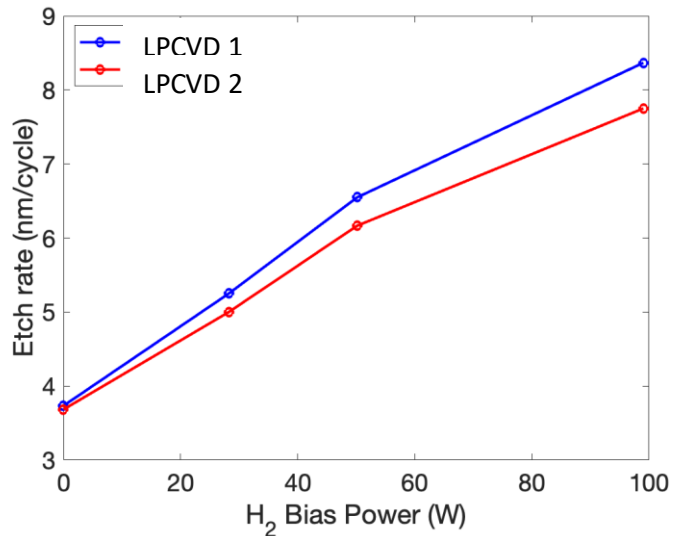


Figure 5: EPC versus H<sub>2</sub> Bias and associated DC Bias

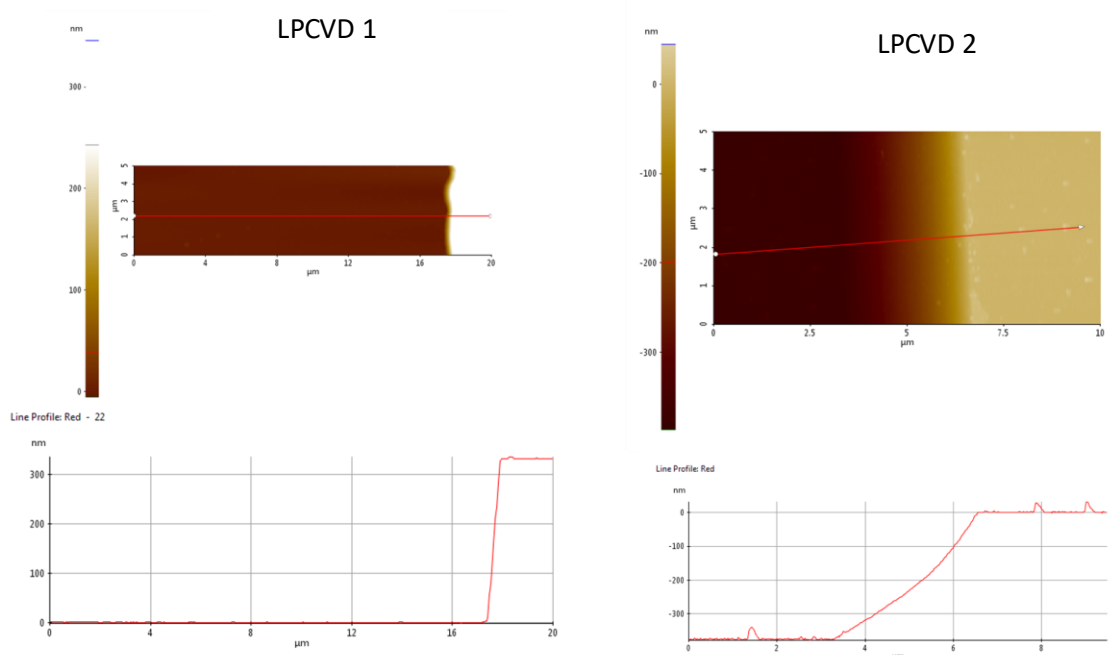
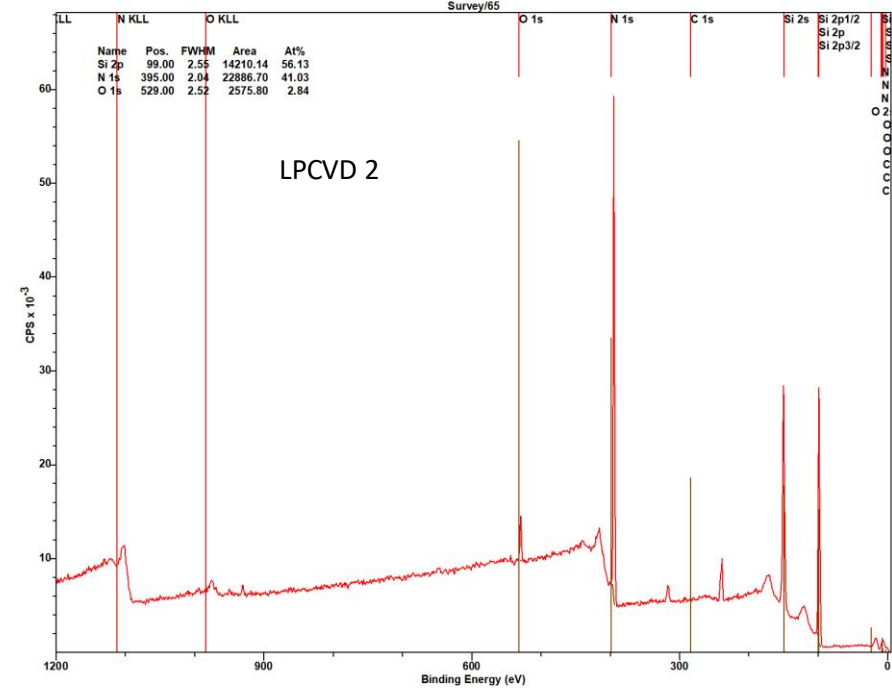
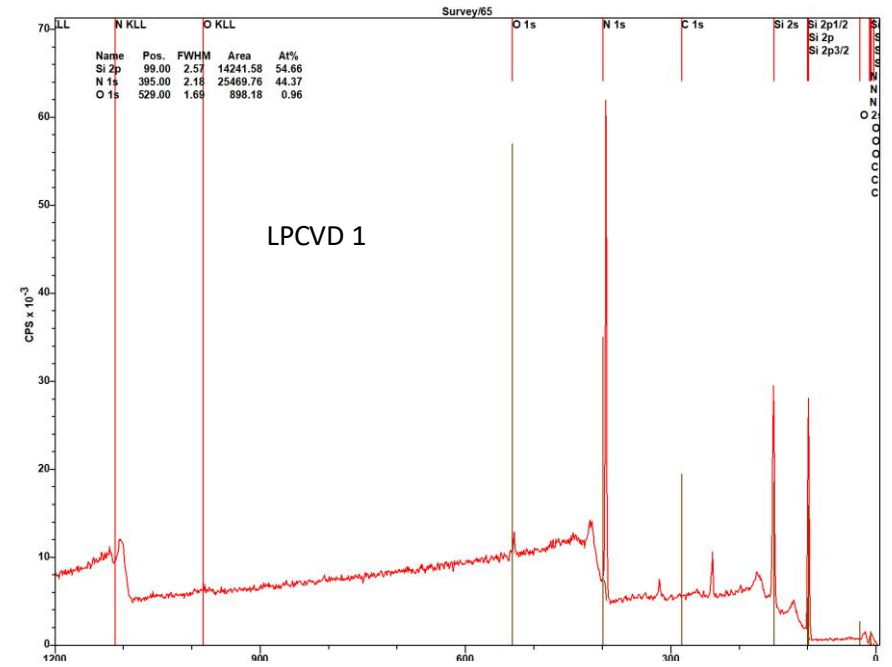


Figure 6: Etch profile for two different LPCVD Silicon Nitride Recipes

Figure 7: XPS Survey spectra for two different LPCVD Silicon Nitride Recipes